

MMBT3904LT1

Preferred Device

General Purpose Transistor

NPN Silicon

Features

- Pb-Free Packages are Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	40	Vdc
Collector–Base Voltage	V_{CBO}	60	Vdc
Emitter–Base Voltage	V_{EBO}	6.0	Vdc
Collector Current – Continuous	I_C	200	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board (Note 1) @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2) @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	–55 to +150	$^\circ\text{C}$

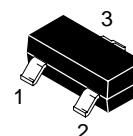
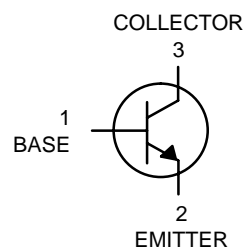
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

- FR–5 = $1.0 \times 0.75 \times 0.062$ in.
- Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.



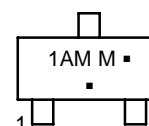
ON Semiconductor®

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SOT–23 (TO–236)
CASE 318
STYLE 6

MARKING DIAGRAM



1AM = Specific Device Code
M = Date Code*
■ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MMBT3904LT1	SOT–23	3000 / Tape & Reel
MMBT3904LT1G	SOT–23 (Pb–Free)	3000 / Tape & Reel
MMBT3904LT3	SOT–23	10,000/Tape & Reel
MMBT3904LT3G	SOT–23 (Pb–Free)	10,000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

MMBT3904LT1

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage ($I_C = 1.0\text{ mAdc}$, $I_B = 0$)	$V_{(BR)CEO}$	40	–	Vdc
Collector–Base Breakdown Voltage ($I_C = 10\ \mu\text{Adc}$, $I_E = 0$)	$V_{(BR)CBO}$	60	–	Vdc
Emitter–Base Breakdown Voltage ($I_E = 10\ \mu\text{Adc}$, $I_C = 0$)	$V_{(BR)EBO}$	6.0	–	Vdc
Base Cutoff Current ($V_{CE} = 30\text{ Vdc}$, $V_{EB} = 3.0\text{ Vdc}$)	I_{BL}	–	50	nAdc
Collector Cutoff Current ($V_{CE} = 30\text{ Vdc}$, $V_{EB} = 3.0\text{ Vdc}$)	I_{CEX}	–	50	nAdc

ON CHARACTERISTICS (Note 3)

DC Current Gain ($I_C = 0.1\text{ mAdc}$, $V_{CE} = 1.0\text{ Vdc}$) ($I_C = 1.0\text{ mAdc}$, $V_{CE} = 1.0\text{ Vdc}$) ($I_C = 10\text{ mAdc}$, $V_{CE} = 1.0\text{ Vdc}$) ($I_C = 50\text{ mAdc}$, $V_{CE} = 1.0\text{ Vdc}$) ($I_C = 100\text{ mAdc}$, $V_{CE} = 1.0\text{ Vdc}$)	H_{FE}	40 70 100 60 30	– – 300 – –	–
Collector–Emitter Saturation Voltage ($I_C = 10\text{ mAdc}$, $I_B = 1.0\text{ mAdc}$) ($I_C = 50\text{ mAdc}$, $I_B = 5.0\text{ mAdc}$)	$V_{CE(sat)}$	– –	0.2 0.3	Vdc
Base–Emitter Saturation Voltage ($I_C = 10\text{ mAdc}$, $I_B = 1.0\text{ mAdc}$) ($I_C = 50\text{ mAdc}$, $I_B = 5.0\text{ mAdc}$)	$V_{BE(sat)}$	0.65 –	0.85 0.95	Vdc

SMALL–SIGNAL CHARACTERISTICS

Current–Gain–Bandwidth Product ($I_C = 10\text{ mAdc}$, $V_{CE} = 20\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	300	–	MHz
Output Capacitance ($V_{CB} = 5.0\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{obo}	–	4.0	pF
Input Capacitance ($V_{EB} = 0.5\text{ Vdc}$, $I_C = 0$, $f = 1.0\text{ MHz}$)	C_{ibo}	–	8.0	pF
Input Impedance ($V_{CE} = 10\text{ Vdc}$, $I_C = 1.0\text{ mAdc}$, $f = 1.0\text{ kHz}$)	h_{ie}	1.0	10	k Ω
Voltage Feedback Ratio ($V_{CE} = 10\text{ Vdc}$, $I_C = 1.0\text{ mAdc}$, $f = 1.0\text{ kHz}$)	h_{re}	0.5	8.0	$\times 10^{-4}$
Small–Signal Current Gain ($V_{CE} = 10\text{ Vdc}$, $I_C = 1.0\text{ mAdc}$, $f = 1.0\text{ kHz}$)	h_{fe}	100	400	–
Output Admittance ($V_{CE} = 10\text{ Vdc}$, $I_C = 1.0\text{ mAdc}$, $f = 1.0\text{ kHz}$)	h_{oe}	1.0	40	μmhos
Noise Figure ($V_{CE} = 5.0\text{ Vdc}$, $I_C = 100\ \mu\text{Adc}$, $R_S = 1.0\text{ k ohms}$, $f = 1.0\text{ kHz}$)	NF	–	5.0	dB

SWITCHING CHARACTERISTICS

Delay Time	$(V_{CC} = 3.0\text{ Vdc}$, $V_{BE} = -0.5\text{ Vdc}$, $I_C = 10\text{ mAdc}$, $I_{B1} = 1.0\text{ mAdc}$)	t_d	–	35	ns
Rise Time		t_r	–	35	
Storage Time	$(V_{CC} = 3.0\text{ Vdc}$, $I_C = 10\text{ mAdc}$, $I_{B1} = I_{B2} = 1.0\text{ mAdc}$)	t_s	–	200	ns
Fall Time		t_f	–	50	

3. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

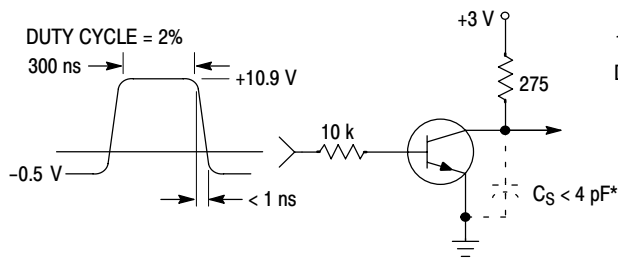


Figure 1. Delay and Rise Time Equivalent Test Circuit

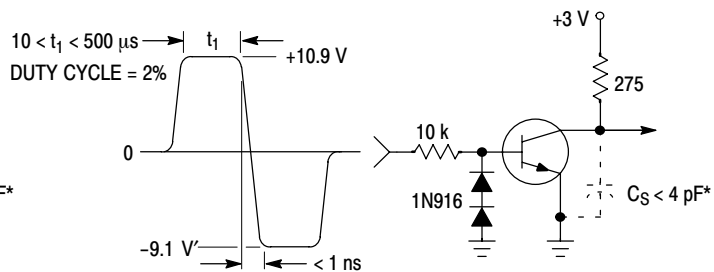


Figure 2. Storage and Fall Time Equivalent Test Circuit

MMBT3904LT1

TYPICAL TRANSIENT CHARACTERISTICS

— $T_J = 25^\circ\text{C}$
 - - - $T_J = 125^\circ\text{C}$

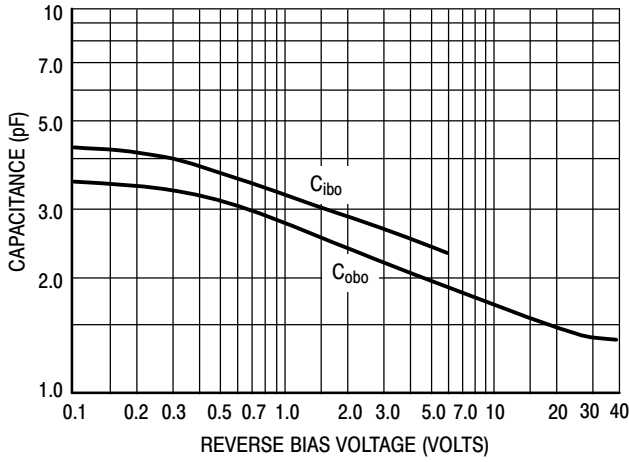


Figure 3. Capacitance

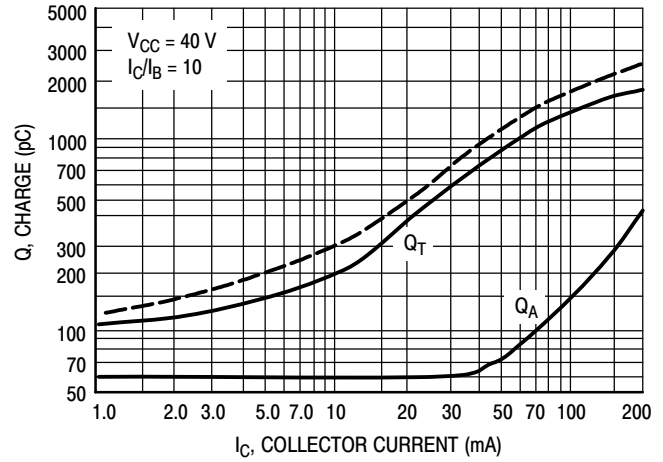


Figure 4. Charge Data

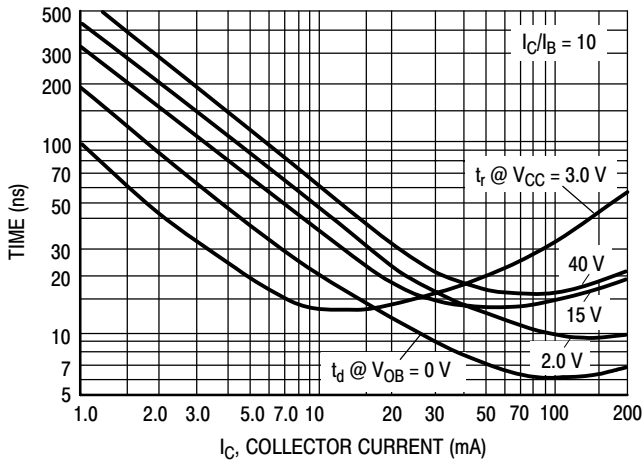


Figure 5. Turn-On Time

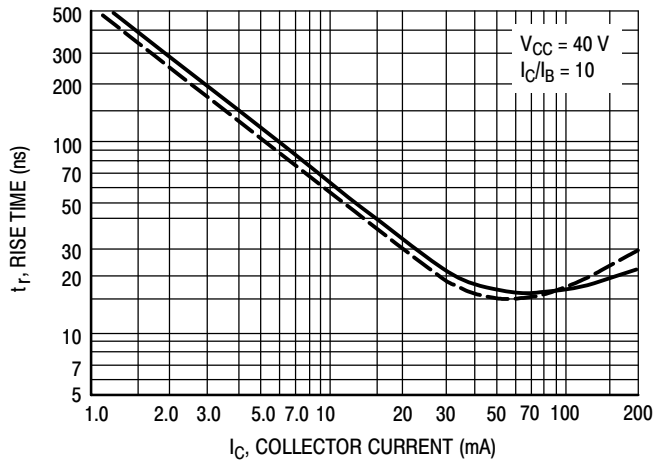


Figure 6. Rise Time

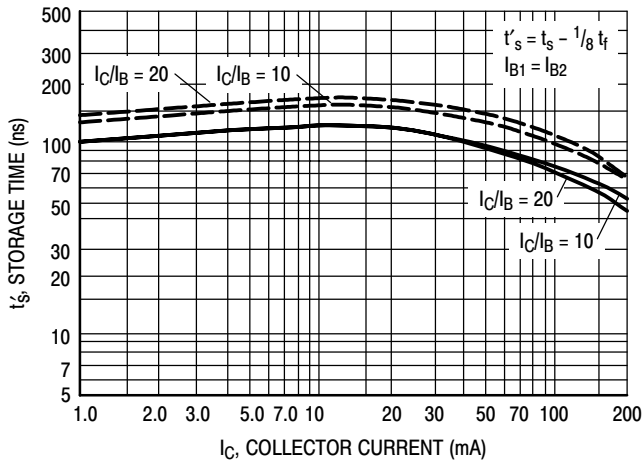


Figure 7. Storage Time

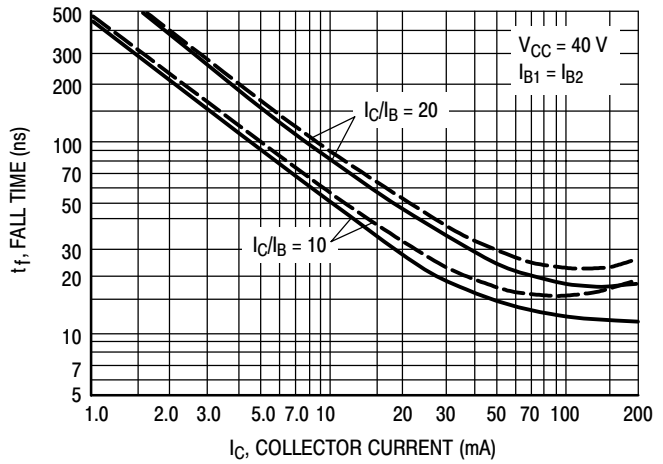


Figure 8. Fall Time

MMBT3904LT1

TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

($V_{CE} = 5.0$ Vdc, $T_A = 25^\circ\text{C}$, Bandwidth = 1.0 Hz)

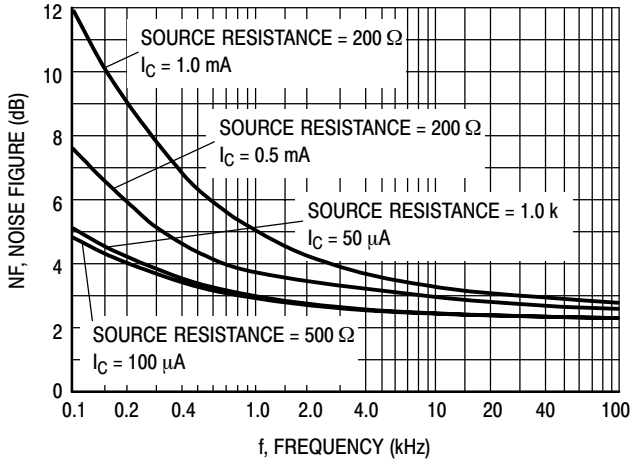


Figure 9.

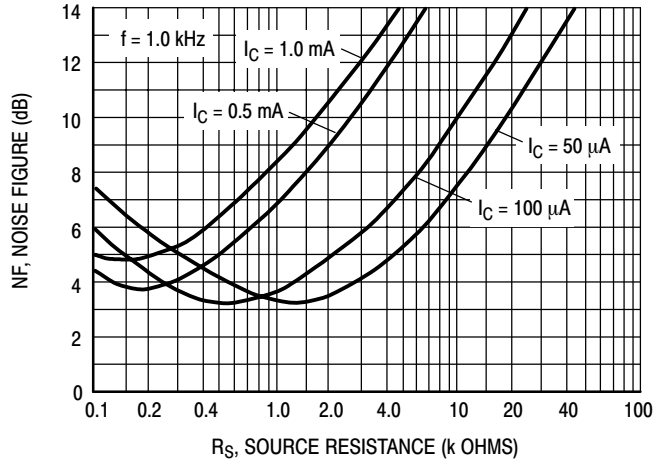


Figure 10.

h PARAMETERS

($V_{CE} = 10$ Vdc, $f = 1.0$ kHz, $T_A = 25^\circ\text{C}$)

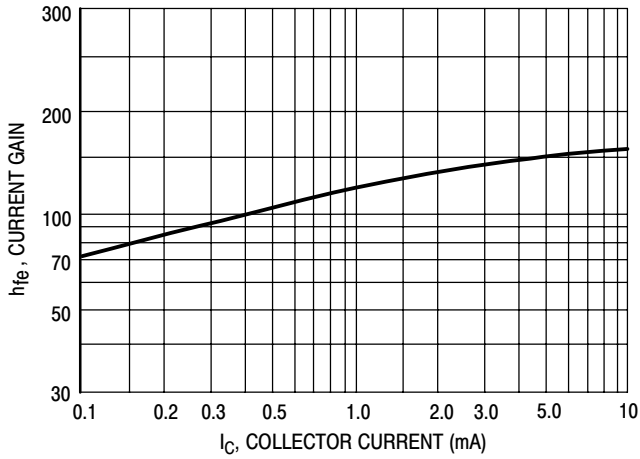


Figure 11. Current Gain

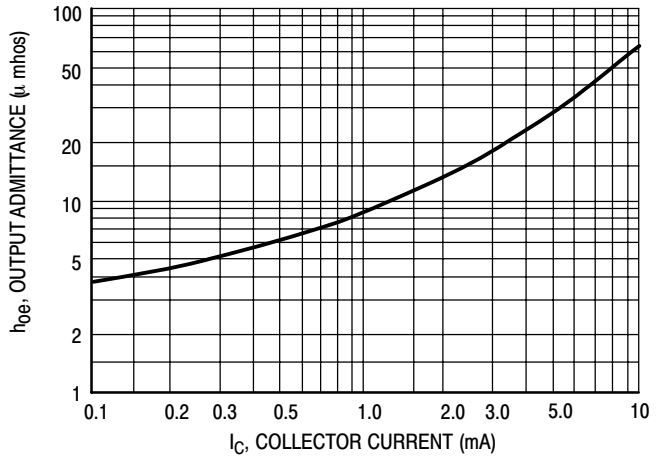


Figure 12. Output Admittance

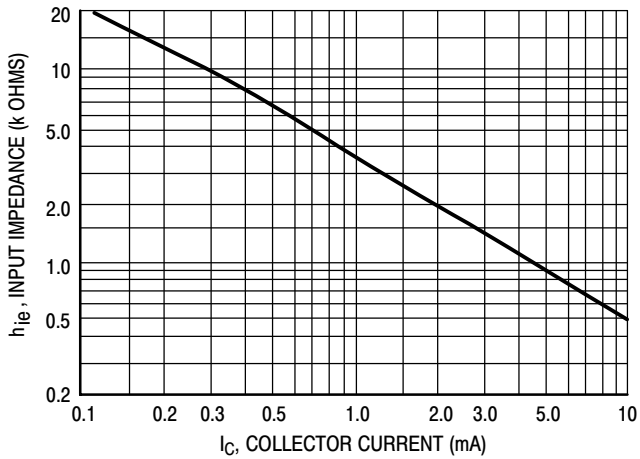


Figure 13. Input Impedance

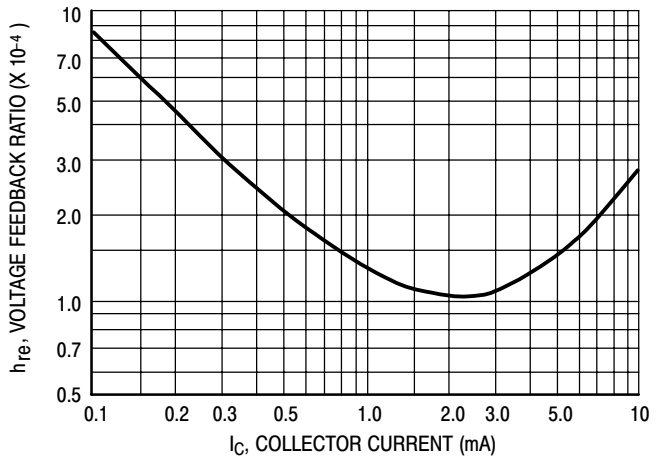


Figure 14. Voltage Feedback Ratio

MMBT3904LT1

TYPICAL STATIC CHARACTERISTICS

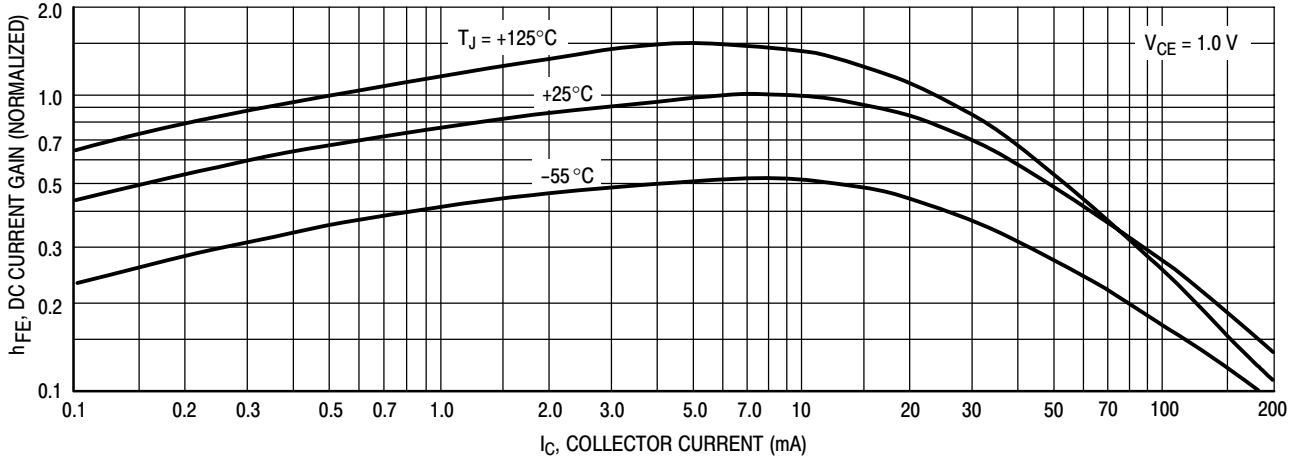


Figure 15. DC Current Gain

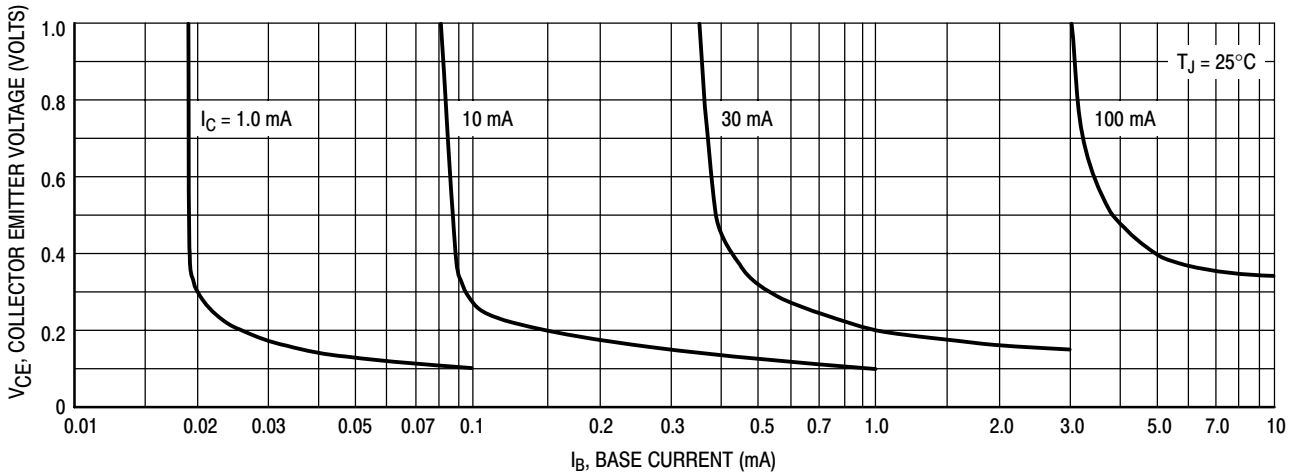


Figure 16. Collector Saturation Region

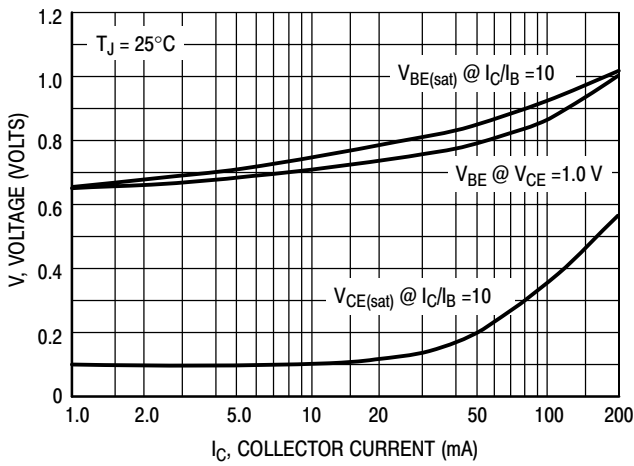


Figure 17. "ON" Voltages

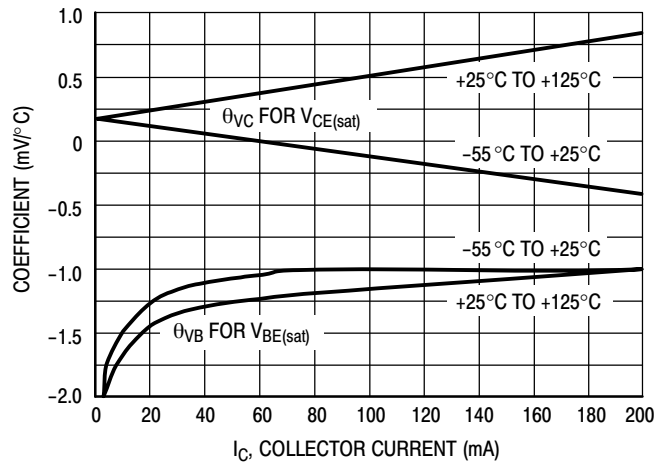
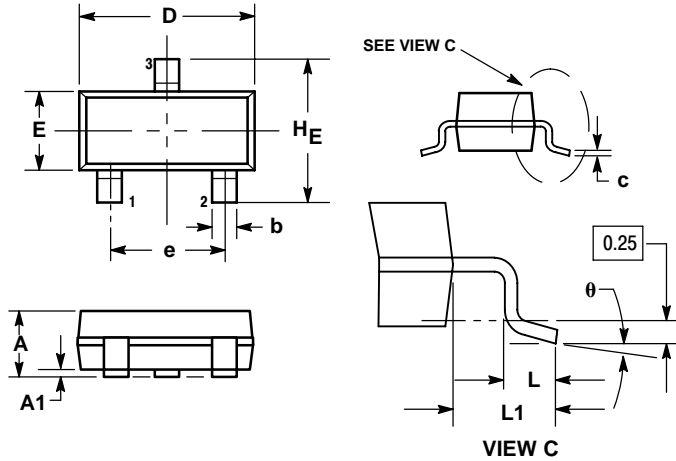


Figure 18. Temperature Coefficients

MMBT3904LT1

PACKAGE DIMENSIONS

SOT-23 (TO-236)
CASE 318-08
ISSUE AN



NOTES:

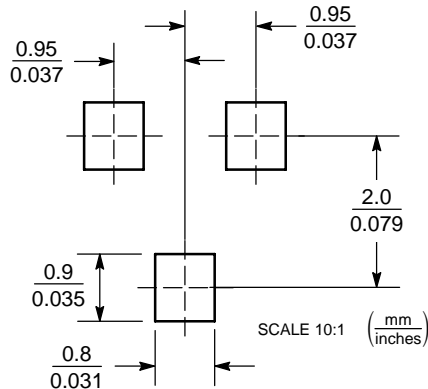
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318-01 THRU -07 AND -09 OBSOLETE, NEW STANDARD 318-08.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104

STYLE 6:

1. BASE
2. EMITTER
3. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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